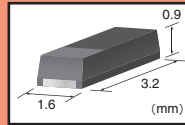
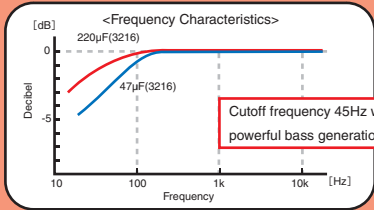


## Tc Chip Tantalum Capacitors

### TCTAS series

- Compact, high capacitance.
- 220µF in the 3216-10[1206] size (AS case) – best in the industry
- Original electrode construction utilized for low ESR and ESL characteristics.

—Ideal for use as coupling capacitors.



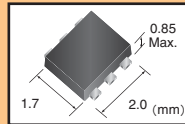
TCTAS

For Audio Circuits

## Tr Complex Bipolar Transistors

### EMX18 (V<sub>CEO</sub>=12V, I<sub>C</sub>=0.5A)

- Low V<sub>CE(sat)</sub>
- Significantly reduces popping noise during power ON.



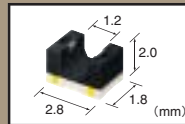
TUMT6

For Muting Circuits

## S Transmission Type Photointerrupters

### NEW RPI-0126

- Ultra-compact surface mount type – 62% smaller in volume than the conventional product (RPI-0125).
- Gap size 1.2mm Ultra-compact while maintaining the same gap size as conventional products.

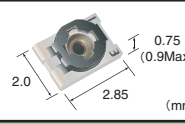


For Cameras

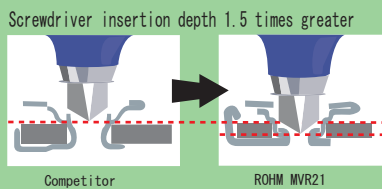
## R Chip Trimmer Potentiometers

### MVR21 series

- Ultra-thin 0.75mm
- Thin and easy to use
- Easy to turn – eliminates the need for a specialized screwdriver.
- Units with a stopper also available that prevents sudden resistance changes, protecting the circuit.



For LCD Backlight



Competitor ROHM MVR21

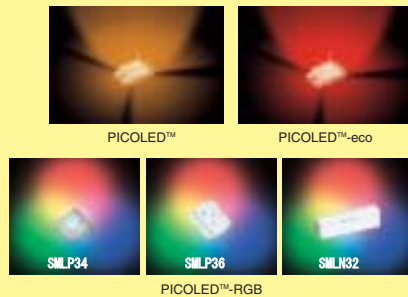
## LED Small & Thin Chip LEDs

### PICOLED™ Series

- <PICOLED™> SML-P12 Series
- 1006 sized package

- <PICOLED™-eco> SML-P11 Series
- 1006 size / low-current type

- <PICOLED™-RGB> SMLP34 / SMLP36 / SMLN32
- World's smallest / thinnest\* 3-in-1 RGB LEDs.



—Narrow-pitched LED matrices are feasible with these LEDs.

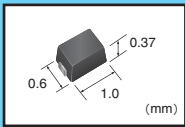
\* September 2007 ROHM Study



## Di Detection Schottky Diodes

### RB886CS

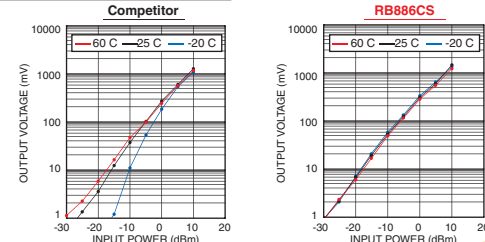
- Superior temperature characteristics: less than ±10%
- Temperature characteristics do not affect the operation environment and the stable output voltage is secured.



VMN2

For RF Circuits

### Temperature Characteristics

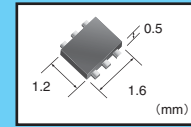


±72% (-10dBm) fluctuation between -20 C and 60 C → ±9.2% (-10dBm) Approximately 1/8\* that of competitor products.

## Di Low Capacitance Zener Diodes

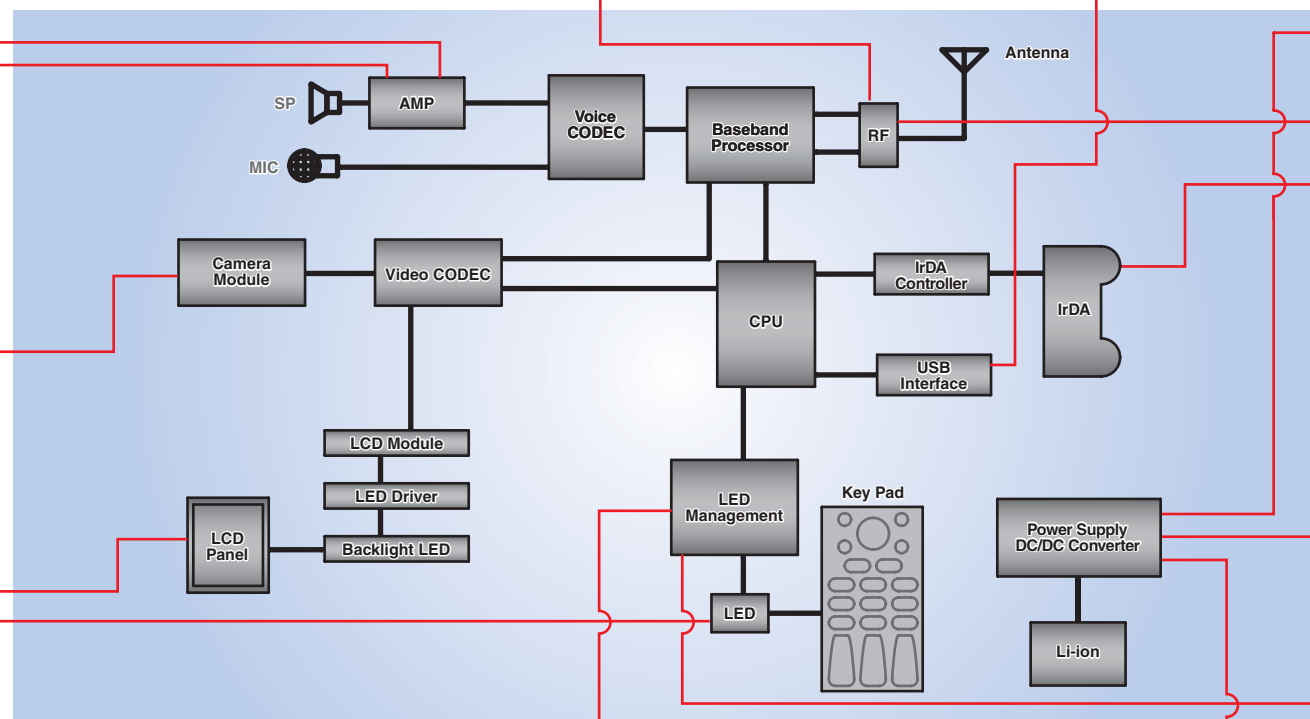
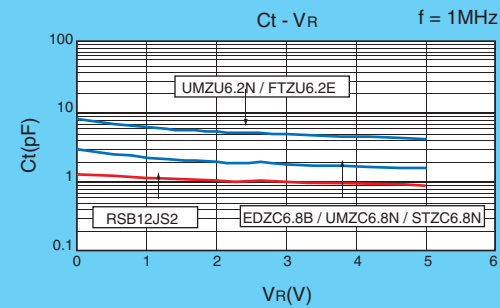
### RSB12JS2 / RSB12W / RSB12Z (V<sub>Z</sub>=9.6 to 14.4V)

- Low C<sub>t</sub> (1pF)
- Low capacitance using ROHM's original technology.



EMD6

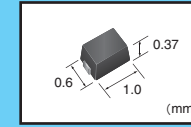
For Interfaces



## Di PIN Diodes

### RN242CS

- Optimal materials and pattern design reduces intermodulation and distortion.



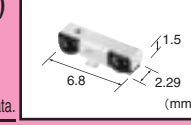
VMN2

For RF Circuits

## IrDA Infrared Communication Modules (FIR-compatible)

### NEW RPM973-H11 (FIR-compatible)

- World's smallest package (ROHM's research)
- Compliant with fastest FIR(4Mbps) standard, which enables high-speed transmission of image data.

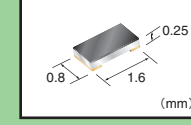


For Interface

## R Ultra Low Ohmic Chip Resistors for Current Detection

### NEW PMR03 series

- Ultra-low ohmic (10 m) resistors in the 1608 [0603] size.
- 0.25W rated power
- Improved power, heat dissipation characteristics due to novel trimless design.
- Superior Temperature Coefficient of Resistance (TCR): ±150ppm/°C
- Special alloy ensures stable low TCR characteristics.



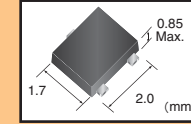
For Power Supply Circuits

## Tr MOSFETs

### RTL030P02 (V<sub>DSS</sub>=-20V, I<sub>D</sub>=-3A)

### NEW RUF015N02 (V<sub>DSS</sub>=20V, I<sub>D</sub>=1.5A)

- Thin high power package (TUMT)
- New lead frame material used for greater power.



For Power Supply Circuits

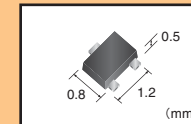
## Tr MOSFETs (1.8V Drive)

### NEW RUM003N02 (V<sub>DSS</sub>=20V, I<sub>D</sub>=0.3A)

### NEW RUE003N02 (V<sub>DSS</sub>=20V, I<sub>D</sub>=0.3A)

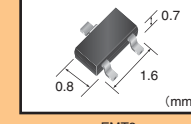
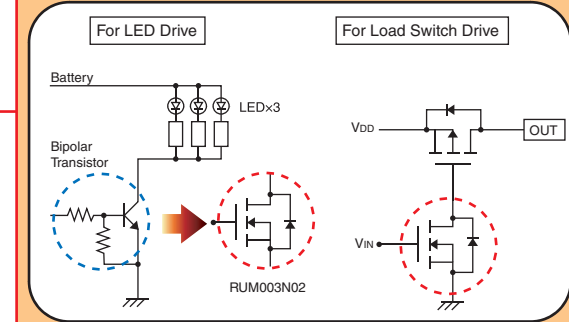
### NEW EM6K6 (V<sub>DSS</sub>=20V, I<sub>D</sub>=0.3A)

- Replacing bipolar transistors with MOSFETs reduces power consumption while simplifying the circuit.



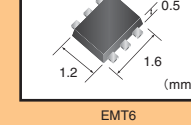
VMT3

For Power Supply Circuits For Driving LEDs



EMT3

For Power Supply Circuits

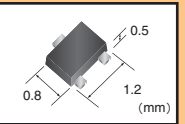


EMT6

## Tr Digital Transistors

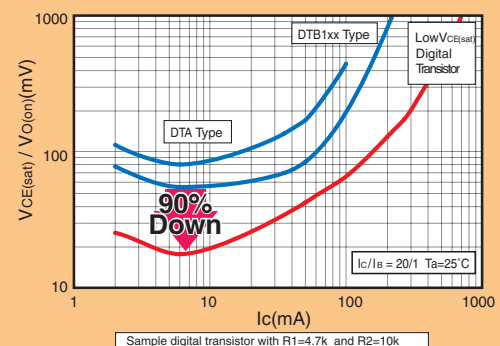
### DTB5□ / DTD5□ series

- Low V<sub>CE(sat)</sub>
- Low power consumption prolongs battery life.



VMT3

For Driving LEDs



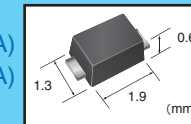
## Di Schottky Barrier Diodes

### RSX101VA-30 (V<sub>RM</sub>=30V, I<sub>O</sub>=1A)

### RSX071VA-30 (V<sub>RM</sub>=30V, I<sub>O</sub>=0.7A)

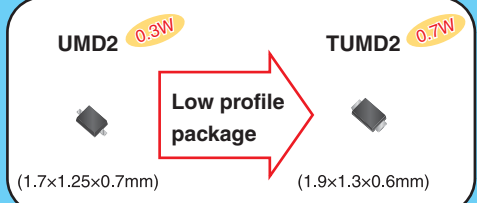
### RSX051VA-30 (V<sub>RM</sub>=30V, I<sub>O</sub>=0.5A)

- Low V<sub>F</sub> & Low I<sub>R</sub>
- High performance achieved utilizing ROHM's original technology.
- Thin high power package (0.7W)
- Greater package power due to underside heat sink configuration.



TUMD2

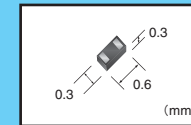
For Power Supply Circuits



## Di Diodes

### GMD2package

- Industry's first smallest package (0.6x0.3mm) for Schottky barrier diode and zener diode.
- This is the tiny package, yet capable to withstand PD=100mW which is industry's top-class package power.



GMD2

